Contribution ID: 47 Type: Poster

Modeling of the bipolar transistor under X-Ray pulse ionizing radiation

Thursday, 13 October 2016 15:15 (30)

This document describes a 2D model of the bipolar transistor 2T312 under X-ray pulse ionizing radiation. Both the Finite Element Discretization and Semiconductor module of Comsol 5.1 are used. We present an analysis of energy deposition in this device under X-ray and the results of transient ionizing current response for some different carrier densities.

Primary author(s): ANTONOVA, Alexandra (National Research Nuclear University MEPhI); Prof. SKO-

ROBOGATOV, Petr (National Research Nuclear University MEPhI)

Presenter(s): ANTONOVA, Alexandra (National Research Nuclear University MEPhI)

Session Classification: Poster session - IV

Track Classification: Methods of experimental physics